

L Number	Hits	Search Text	DB	Time stamp
2	16	MBE same alternat\$3 with beam?	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 11:31
3	13	(MBE same alternat\$3 with beam?) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 11:33
5	1	((MBE same alternat\$3 with beam?) and @ad<20010323) and (aluminum Al) same (nitrogen N2 "n.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 11:36

L Number	Hits	Search Text	DB	Time stamp
1	320	heterojunction and (aluminum adj nitride AlN with passivat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:10
2	212	((heterojunction and (aluminum adj nitride AlN with passivat\$3)) and MBE	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:06
3	66	((heterojunction and (aluminum adj nitride AlN with passivat\$3)) and MBE) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:11
4	136	(aluminum adj nitride AlN) with passivat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 14:22
5	1	((aluminum adj nitride AlN) with passivat\$3) same heterojunction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:17
6	6	((aluminum adj nitride AlN) with passivat\$3) and heterojunction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:11
7	4	((aluminum adj nitride AlN) with passivat\$3) and heterojunction) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:55
8	4	((aluminum adj nitride AlN) with passivat\$3) same GaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:19
9	0	((aluminum adj nitride AlN) with passivat\$3) and GaN near5 FET?	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:20
10	6	((aluminum adj nitride AlN) with passivat\$3) and GaN near5 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:20
11	1	((aluminum adj nitride AlN) with passivat\$3) and GaN near5 substrate) and HFET?	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:21
12	4	((aluminum adj nitride AlN) with passivat\$3) and GaN near5 substrate) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:51

13	2	((aluminum adj nitride AlN) with passivat\$3) same transistor?	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:50
14	1	((aluminum adj nitride AlN) with passivat\$3) same MBE	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:50
15	5	(aluminum adj nitride AlN) with surface with transistor?	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 14:16
16	4	((aluminum adj nitride AlN) with surface with transistor?) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 13:51
17	118	((aluminum adj nitride AlN) with passivat\$3) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 14:17
18	4	((aluminum adj nitride AlN) with passivat\$3) and @ad<20010323) and heterojunction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 14:01
19	1	("5637146").PN.	USPAT	2003/04/24 14:01
20	17	(aluminum adj nitride AlN) with surface same transistor?	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 14:17
21	16	((aluminum adj nitride AlN) with surface same transistor?) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 14:24
22	1	((aluminum adj nitride AlN) with passivat\$3) with field adj effect	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 14:23
23	37	((aluminum adj nitride AlN) with passivat\$3) with surface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 14:24
24	35	((aluminum adj nitride AlN) with passivat\$3) with surface) and @ad<20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/24 14:24